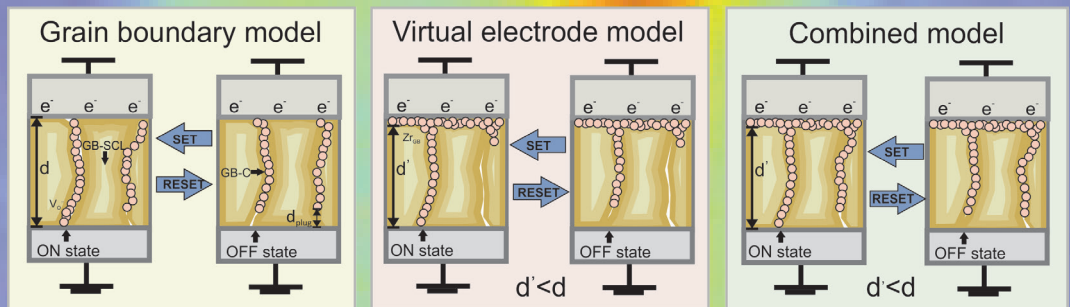




Resistive switching in ZrO_2 based metal-oxide-metal structures

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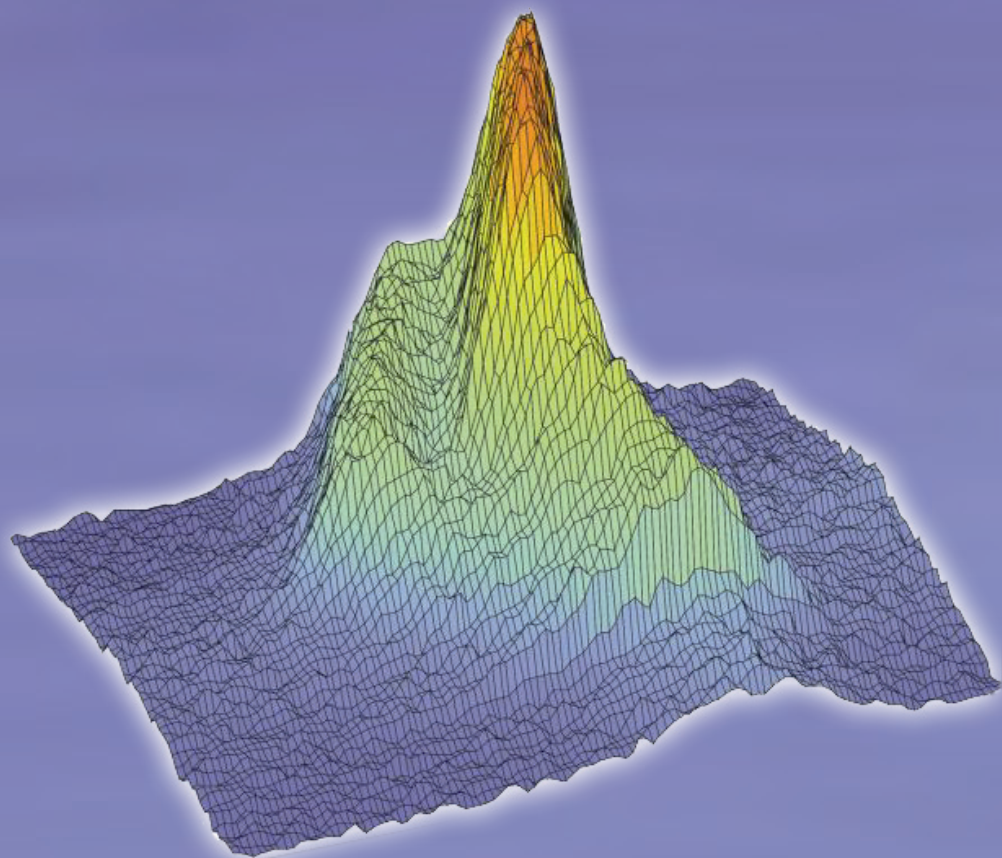
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